

High voltage power Schottky rectifier

Main product characteristics

$I_{F(AV)}$	2 x 7.5 A
V_{RRM}	100 V
T_j (max)	175° C
V_F (max)	0.67 V

Features and Benefits

- Negligible switching losses
- Low leakage current
- Good trade off between leakage current and forward voltage drop
- Low thermal resistance
- Avalanche capability specified

Description

Dual center tab Schottky rectifier suited for switched mode power supply and high frequency DC to DC converters.

Packaged in DPAK and IPAK, this device is intended for use in high frequency inverters.

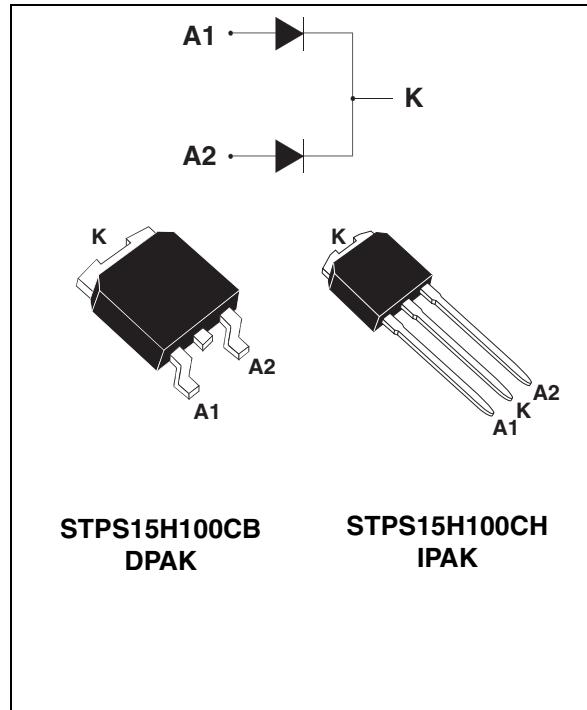


Table 1. Absolute Ratings (limiting values, per diode)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			100	V
$I_{F(RMS)}$	RMS forward current			10	A
$I_{F(AV)}$	Average forward current	$T_c = 135^\circ C$	Per diode	7.5	A
		$\delta = 0.5$	Per device	15	
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms sinusoidal}$		75	A
I_{RRM}	Peak repetitive reverse current	$t_p = 2 \mu\text{s square } F = 1 \text{ kHz}$		1	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1 \mu\text{s } T_j = 25^\circ C$		6600	W
T_{stg}	Storage temperature range			-65 to + 175	°C
T_j	Maximum operating junction temperature ⁽¹⁾			175	°C
dV/dt	Critical rate of rise of reverse voltage			10000	V/μs

1. $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ condition to avoid thermal runaway for a diode on its own heatsink

1 Characteristics

Table 2. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	4
		Total	2.4
$R_{th(c)}$	Coupling	0.7	

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25^\circ C$	$V_R = V_{RRM}$			3	μA
		$T_j = 125^\circ C$			1.3	4	mA
$V_F^{(1.)}$	Forward voltage drop	$T_j = 25^\circ C$	$I_F = 7.5 A$			0.8	V
		$T_j = 125^\circ C$	$I_F = 7.5 A$		0.62	0.67	
		$T_j = 25^\circ C$	$I_F = 12 A$			0.85	
		$T_j = 125^\circ C$	$I_F = 12 A$		0.68	0.73	
		$T_j = 25^\circ C$	$I_F = 15 A$			0.89	
		$T_j = 125^\circ C$	$I_F = 15 A$		0.71	0.76	

1. Pulse test: $t_p = 380 \mu s$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.58 \times I_{F(AV)} + 0.012 I_F^2 (\text{RMS})$$

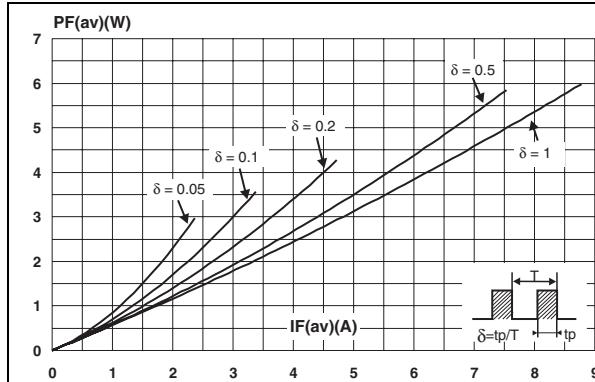
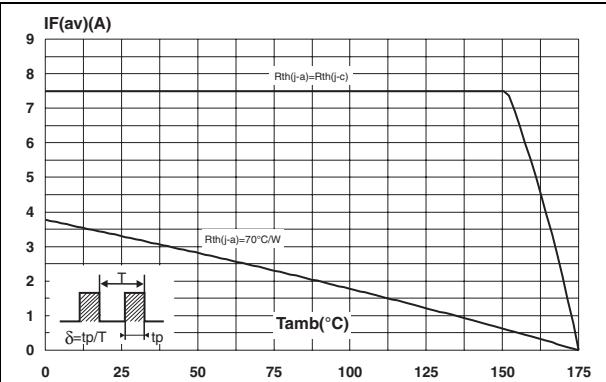
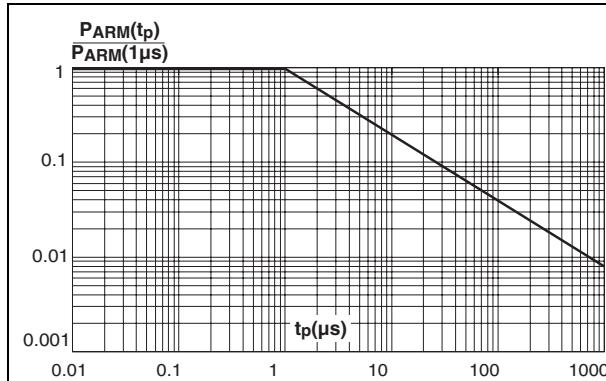
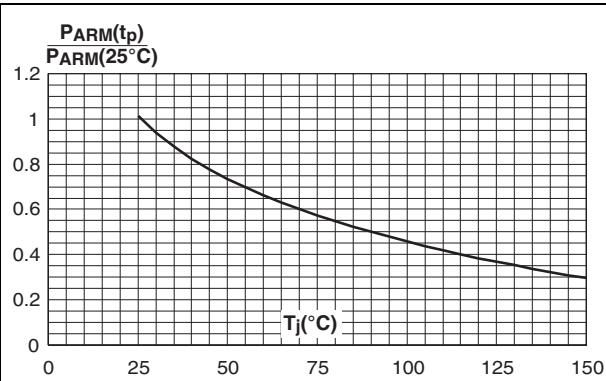
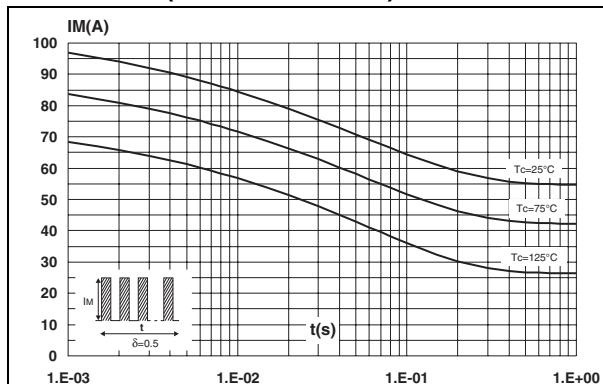
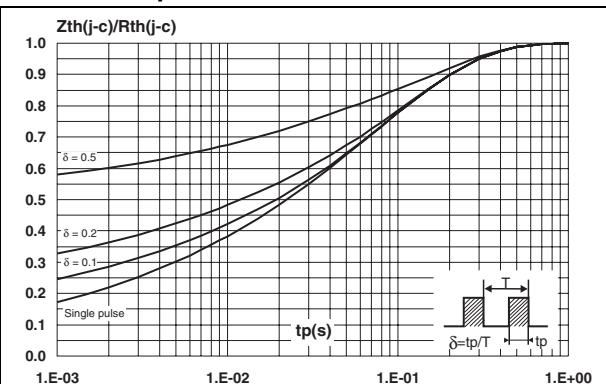
Figure 1. Conduction losses versus average current**Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$)****Figure 3. Normalized avalanche power derating versus pulse duration****Figure 4. Normalized avalanche power derating versus junction temperature****Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values)****Figure 6. Relative variation of thermal impedance junction to case versus pulse duration**

Figure 7. Reverse leakage current versus reverse voltage applied (typical values)

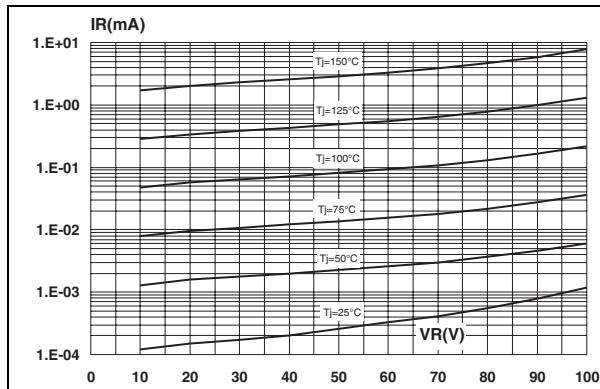


Figure 8. Junction capacitance versus reverse voltage applied (typical values)

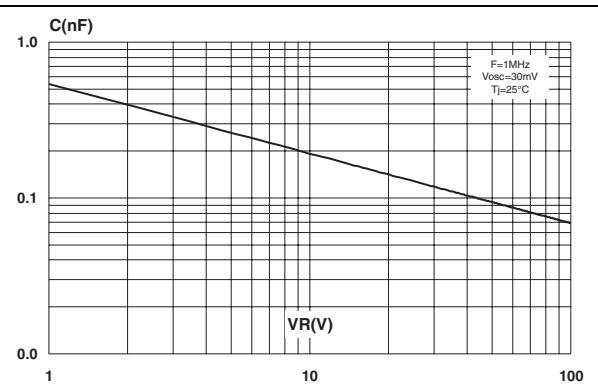


Figure 9. Forward voltage drop versus forward current

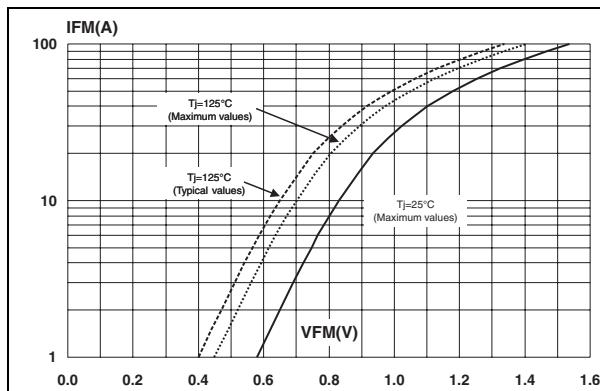
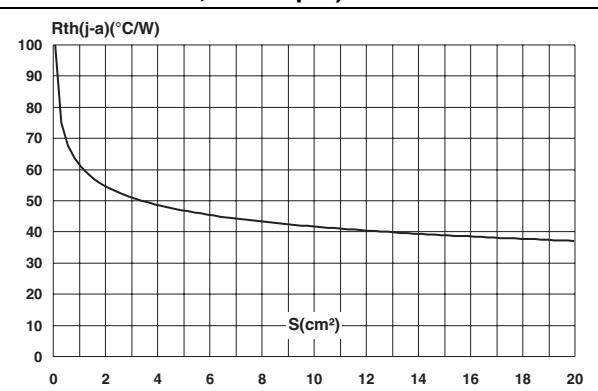


Figure 10. Thermal resistance junction to ambient versus copper surface under tab (epoxy printed board FR4, Cu: 35μm)



2 Package Information

Epoxy meets UL94,V0

Table 4. DPAK Package mechanical data

Ref	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.20	2.40	0.086	0.094
A1	0.90	1.10	0.035	0.043
A2	0.03	0.23	0.001	0.009
B	0.64	0.90	0.025	0.035
B2	5.20	5.40	0.204	0.212
C	0.45	0.60	0.017	0.023
C2	0.48	0.60	0.018	0.023
D	6.00	6.20	0.236	0.244
E	6.40	6.60	0.251	0.259
G	4.40	4.60	0.173	0.181
H	9.35	10.10	0.368	0.397
L2	0.80 typ.		0.031 typ.	
L4	0.60	1.00	0.023	0.039
V2	0°	8°	0°	8°

Figure 11. DPAK Footprint (dimensions in mm)

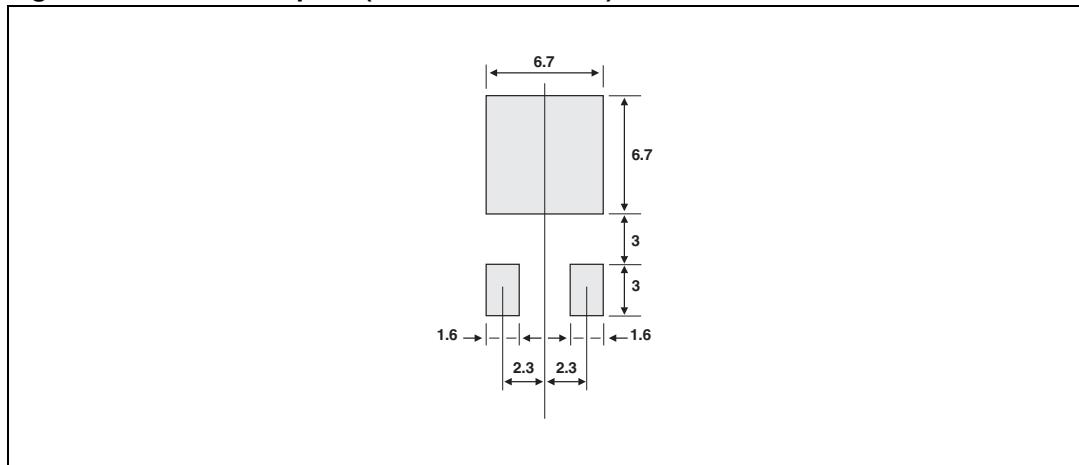
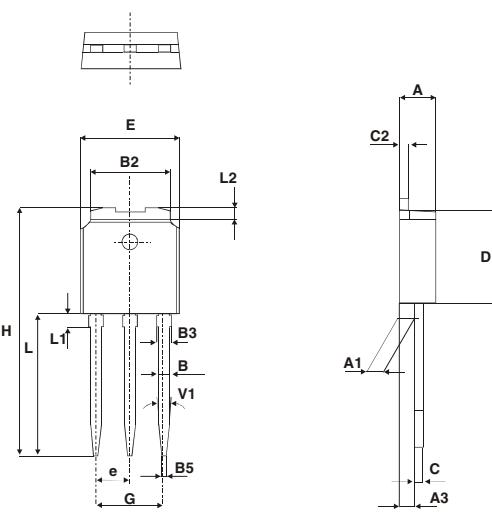


Table 5. IPAK Package mechanical data

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.094
A1	0.90		1.10	0.035		0.043
A3	0.70		1.30	0.027		0.051
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.212
B3			0.95			0.037
B5		0.30			0.035	
C	0.45		0.60	0.017		0.023
C2	0.48		0.60	0.019		0.023
D	6		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
e		2.28			0.090	
G	4.40		4.60	0.173		0.181
H		16.10			0.634	
L	9		9.40	0.354		0.370
L1	0.8		1.20	0.031		0.047
L2		0.80	1		0.031	0.039
V1			10°			10°



The technical drawings illustrate the physical dimensions of the IPAK package. The front view shows the overall height H, lead pitch L, lead width L1, lead height L2, and lead angle V1. The top view shows the chip size E, bond pad widths B2 and B3, and bond pad height B5. The side view provides a detailed look at the lead profile, including lead thickness A, lead height C2, lead width D, lead angle A1, and lead bottom width A3.

3 Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS15H100CB	S15H100	DPAK	0.30 g	75	Tube
STPS15H100CB-TR	S15H100	DPAK	0.30 g	2500	Tape and reel
STPS15H100CH	S15H100CH	IPAK	0.35 g	75	Tube

4 Revision History

Date	Revision	Changes
Mar-2004	3	Last issue
08-Jun-2006	4	Reformatted to current standard. Added IPAK.

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